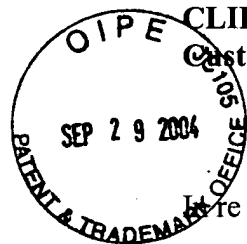


JFH  
PATENT

DOCKET NO.: P05810  
CLIENT NO.: NATI15-05810  
Customer No.: 23990



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : RICHARD W. FOOTE  
U.S. Serial No. : 10/781,166  
Filed : February 18, 2004  
For : SYSTEM AND METHOD FOR PROVIDING A UNIFORM OXIDE  
LAYER OVER A LASER TRIMMED FUSE WITH A  
DIFFERENTIAL WET ETCH STOP TECHNIQUE  
Group No. : 2829  
Examiner : Not Yet Assigned

**MAIL STOP AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**CERTIFICATE OF MAILING BY FIRST CLASS MAIL**

The undersigned hereby certifies that the following documents:

1. Postcard receipt;
2. Information Disclosure Statement;
3. Forms PTO/SB/08A and PTO/SB/08B; and
4. Thirty-three (33) references.

relating to the above application, were deposited as "First Class Mail" with the United States Postal Service, addressed to, MAIL STOP AMENDMENT, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on Sept 27, 2004.

Date: Sept 27, 2004

Kathy Hamilton  
Mailer

Date: Sept 24, 2004

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P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

INFORMATION DISCLOSURE STATEMENT

Pursuant to the duty of disclosure under 37 C.F.R. § 1.56, Applicant submits this statement. This submittal is made in accordance with 37 C.F.R. §§ 1.97 and 1.98 and § 609 of the Manual of Patent Examining Procedure. The patents and publications herein are listed below and on the attached Forms PTO/SB/08A and PTO/SB/08B. Copies of the listed patents and publications are submitted herewith.

<u>U.S. Patent No.</u>	<u>Inventor</u>	<u>Date</u>
4,217,570	Holmes	August 12, 1980
4,413,272	Mochizuki et al.	November 1, 1983
4,455,194	Yabu et al.	June 19, 1984

4,602,420	Saito	July 29, 1986
5,096,850	Lippitt, III	March 17, 1992
5,232,874	Rhodes et al.	August 3, 1993
5,235,205	Lippitt, III	August 10, 1993
5,258,096	Sandhu et al.	November 2, 1993
5,538,924	Chen	July 23, 1996
5,585,662	Ogawa	December 17, 1996
5,598,027	Matsuura	January 28, 1997
5,821,160	Rodriguez et al.	October 13, 1998
5,872,390	Lee et al.	February 16, 1999
5,895,963	Yamazaki	April 20, 1999
6,017,824	Lee et al.	January 25, 2000
6,025,214	Reddy et al.	February 15, 2000
6,046,488	Kawasaki et al.	April 4, 2000
6,100,116	Lee et al.	August 8, 2000
6,180,503	Tzeng et al.	January 30, 2001
6,294,474	Tzeng et al.	September 25, 2001
6,307,213	Huang et al.	October 23, 2001
6,399,472	Suzuki et al.	June 4, 2002
6,617,664	Hayashi et al.	September 9, 2003
6,677,226	Bowen et al.	January 13, 2004

#### Publications

Simon S. Cohen et al., "Laser-Induced Melting of Thin Conducting Films: Part I-The Adiabatic Approximation", IEEE Transactions on Electron Devices, Vol. 38, No. 9, September 1991, Pp. 2042-2050.

Joseph B. Bernstein et al., "Laser Energy Limitation for Buried Metal Cuts" IEEE Electron Device Letters, Vol. 19, No 1, January 1998, Pp. 4-6.

Simon S. Cohen et al., "Laser-Induced Melting of Thin Conducting Films: Part II-Heat-Dissipating Substrates", IEEE Transactions on Electron Devices, Vol. 38, No. 9, September 1991, Pp. 2051-2057.

Will R. Moore, "A Review of Fault-Tolerant Techniques for the Enhancement of Integrated Circuit Yield", Proceedings of the IEEE, Vol. 74, No. 5, May 1986, Pp. 684-698.

Yunlong Sun et al., "Optimization of Memory Redundancy Laser Link Processing", SPIE Vol. 2636, Pp. 152-164.

Don Smart et al., "Link Processing with Lasers", General Scanning Inc. 1998, Pp. 1-20.

Ronald P. Cenker et al., "A Fault-Tolerant 64K Dynamic Random-Access Memory", IEEE Transactions on Electron Devices, Vol. ED-26, No. 6, June 1979, Pp. 853-860.

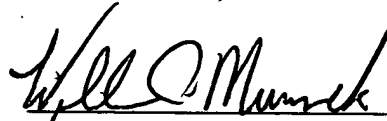
A. S. Tenney et al., "Etch Rates of Doped Oxides in Solutions of Buffered HF", J. Electrochem Soc.: Solid-State Science and Technology, August 1973, Pp. 1091-1095.

Gang Yang, "Laser Energy Window Simulation for Metal Cut Structure" Thesis for the Degree of Master of Science, University of Maryland, 1999, 104 pages.

Applicant hereby expressly reserves the right to swear behind the effective dates of any of the above Patents and to question the relevance and materiality of the Patents and Publications listed herein, in whole, in part, or in combination, subsequent to filing this Information Disclosure Statement.

Respectfully submitted,

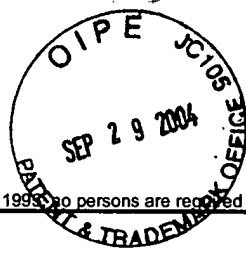
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William A. Munck  
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PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031  
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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 1 of 3

**Complete if Known**

Application Number	10/781,166
Filing Date	February 18, 2004
First Named Inventor	Richard W. Foote
Art Unit	2829
Examiner Name	Not Yet Assigned
Attorney Docket Number	P05810

**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	AA	US- 4,217,570	08/12/1980	Holmes	
	AB	US- 4,413,272	11/01/1983	Mochizuki et al.	
	AC	US- 4,455,194	06/19/1984	Yabu et al.	
	AD	US- 4,602,420	07/29/1986	Saito	
	AE	US- 5,096,850	03/17/1992	Lippitt, III	
	AF	US- 5,232,874	08/03/1993	Rhodes et al.	
	AG	US- 5,235,205	08/10/1993	Lippitt, III	
	AH	US- 5,258,096	11/02/1993	Sandhu et al.	
	AI	US- 5,538,924	07/23/1996	Chen	
	AJ	US- 5,585,662	12/17/1996	Ogawa	
	AK	US- 5,598,027	01/28/1997	Matsuura	
	AL	US- 5,821,160	10/13/1998	Rodriguez et al.	
	AM	US- 5,872,390	02/16/1999	Lee et al.	
	AN	US- 5,895,963	04/20/1999	Yamazaki	
	AO	US- 6,017,824	01/25/2000	Lee et al.	
	AP	US- 6,025,214	02/15/2000	Reddy et al.	
	AQ	US- 6,046,488	04/04/2000	Kawasaki et al.	
	AR	US- 6,100,116	08/08/2000	Lee et al.	
	AS	US- 6,180,503	01/30/2001	Tzeng et al.	

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				

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SignatureDate  
Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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**INFORMATION DISCLOSURE  
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Application Number	10/781,166
Filing Date	February 18, 2004
First Named Inventor	Richard W. Foote
Art Unit	2829
Examiner Name	Not Yet Assigned
Attorney Docket Number	P05810

Sheet 2 of 3**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	BA	US- 6,294,474	09/25/2001	Tzeng et al.	
	BB	US- 6,307,213	10/23/2001	Huang et al.	
	BC	US- 6,399,472	06/04/2002	Suzuki et al.	
	BD	US- 6,617,664	09/09/2003	Hayashi et al.	
	BE	US- 6,677,226	01/13/2004	Bowen et al.	
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		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				

Examiner  
SignatureDate  
Considered

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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				Art Unit	2829
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	P05810

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	Simon S. Cohen et al., "Laser-Induced Melting of Thin Conducting Films: Part I-The Adiabatic Approximation", IEEE Transactions on Electron Devices, Vol. 38, No. 9, September 1991, Pp. 2042-2050.	
	CB	Joseph B. Bernstein et al., "Laser Energy Limitation for Buried Metal Cuts" IEEE Electron Device Letters, Vol. 19, No 1, January 1998, Pp. 4-6.	
	CC	Simon S. Cohen et al., "Laser-Induced Melting of Thin Conducting Films: Part II-Heat-Dissipating Substrates", IEEE Transactions on Electron Devices, Vol. 38, No. 9, September 1991, Pp. 2051-2057.	
	CD	Will R. Moore, "A Review of Fault-Tolerant Techniques for the Enhancement of Integrated Circuit Yield", Proceedings of the IEEE, Vol. 74, No. 5, May 1986, Pp. 684-698.	
	CE	Yunlong Sun et al., "Optimization of Memory Redundancy Laser Link Processing", SPIE Vol. 2636, Pp. 152-164.	
	CF	Don Smart et al., "Link Processing with Lasers", General Scanning Inc. 1998, Pp. 1-20.	
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	CH	A. S. Tenney et al., "Etch Rates of Doped Oxides in Solutions of Buffered HF", J. Electrochem Soc.: Solid-State Science and Technology, August 1973, Pp. 1091-1095.	
	CI	Gang Yang, "Laser Energy Window Simulation for Metal Cut Structure" Thesis for the Degree of Master of Science, University of Maryland, 1999, 104 pages.	

Examiner Signature		Date Considered	
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